

AO8801-VB Datasheet

Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 30	0.036 at V _{GS} = - 10 V	- 5.2		
	0.055 at V _{GS} = - 4.5 V	- 4.2		

FEATURES

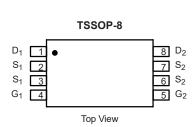
- · Halogen-free
- TrenchFET® Power MOSFETs

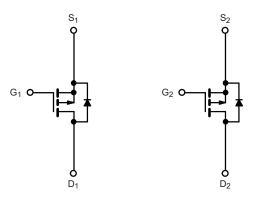


ROHS

APPLICATIONS

- · Load Switch
- · Battery Switch





P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise r	noted		_
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 30		V
Gate-Source Voltage		V_{GS}	± 20		V
0 11 0 17 17000	T _A = 25 °C	- I _D	- 5.2	- 4.1	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 4.2	- 3.6	•
Pulsed Drain Current (10 µs Pulse Width)		I _{DM}	- 30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.0	- 0.70	
M	T _A = 25 °C	P _D	1.14	0.83	W
Maximum Power Dissipation ^a	T _A = 70 °C		0.73	0.53	
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55	to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	86	110	
	Steady State		124	150	°C/W
Maximum Junction-to-Foot	Steady State	R _{thJF}	52	65	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

服务热线:400-655-8788

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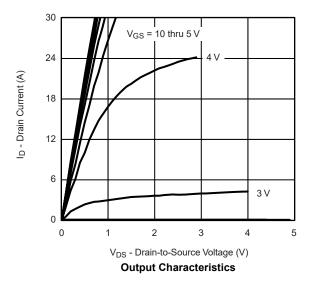
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current		V _{DS} = - 30 V, V _{GS} = 0 V			- 1	μA
	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 15			Α
Drain-Source On-State Resistance ^a		V _{GS} = - 10 V, I _D = - 4.7 A		0.036		
	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 3.8 A		0.055		Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 4.7 A		14		S
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.0 A, V _{GS} = 0 V		- 0.74	- 1.1	V
Dynamic ^b				'	•	
Total Gate Charge	Qg			13	20	
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.7 \text{ A}$		3		nC
Gate-Drain Charge	Q_{gd}			5.8		
Gate Resistance	R_{g}	f = 1.0 MHz		4.6		Ω
Turn-On Delay Time	t _{d(on)}			13	20	
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		14	22	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 10 V, R_G = 6 Ω		52	80	ns
Fall Time	t _f			26	40	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.0 A, dl/dt = 100 A/μs		40	60	

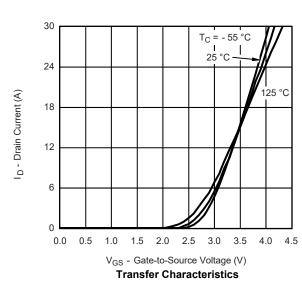
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

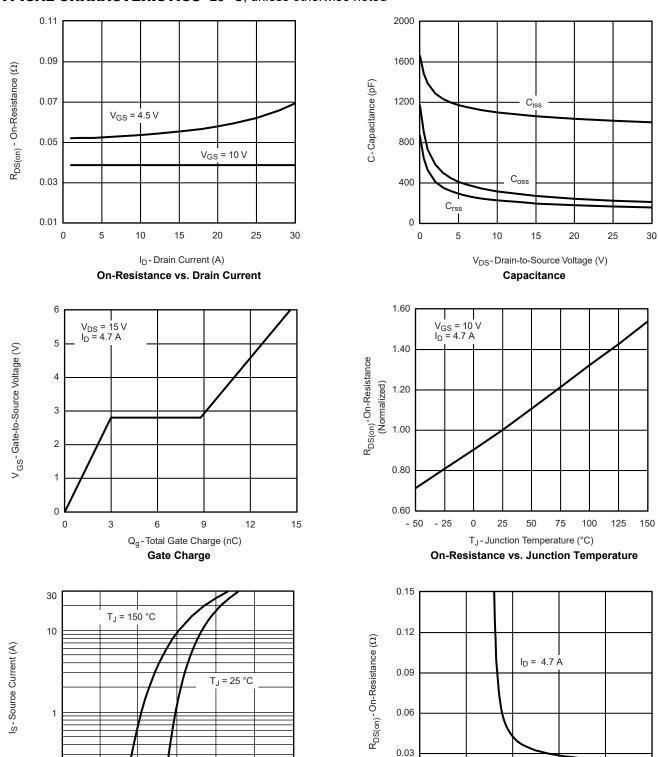
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



0.00

0

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0.1 -

0.3

0.6

0.9

V_{SD}-Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

1.2

1.5

8

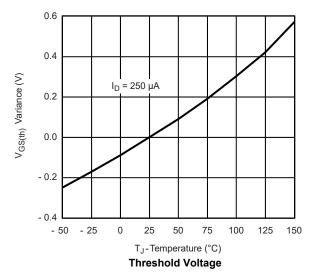
V_{GS}- Gate-to-Source Voltage (V)

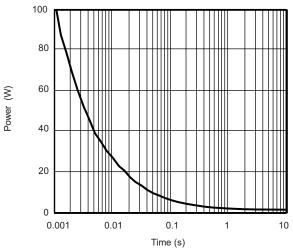
On-Resistance vs. Gate-to-Source Voltage

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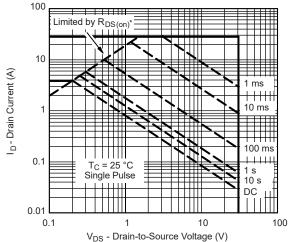


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

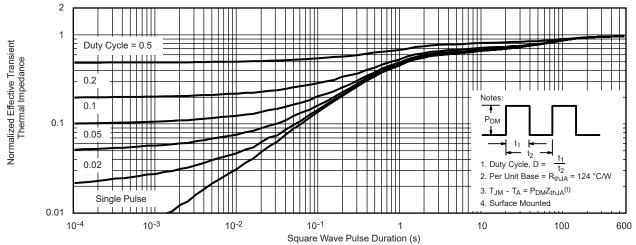




Single Pulse Power, Junction-to-Ambient



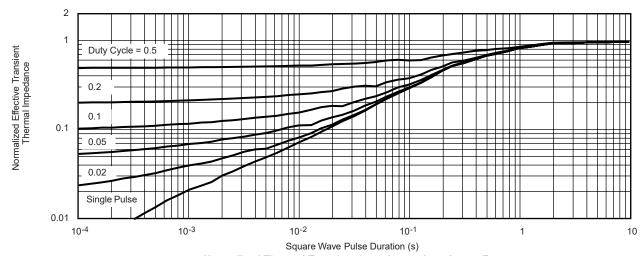
 * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified **Safe Operating Area, Junction-to-Case**



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

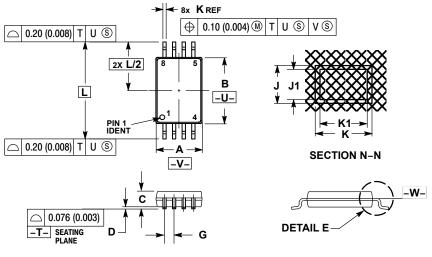


Normalized Thermal Transient Impedance, Junction-to-Foot



TSSOP-8





	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	4.30	4.50	0.169	0.177
U		1.10		0.043
D	0.05	0.15	0.002	0.006
F	0.50	0.70	0.020	0.028
G	0.65 BSC		0.026 BSC	
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252	
M	0°	8°	0	8 °

N 🚤	0.25 (0.010)		
N	M		

DETAIL E



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